



Micro Commercial Components



Micro Commercial Components  
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# MC7252KDW

## N-Channel P-Channel Power MOSFET

### Features

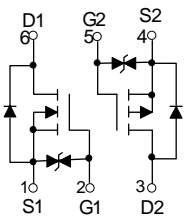
- Halogen free available upon request by adding suffix "-HF"
- High-Side Switching
- Low Threshold
- Lead Free Finish/RoHS Compliant ("P" Suffix designates RoHS Compliant. See ordering information)
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

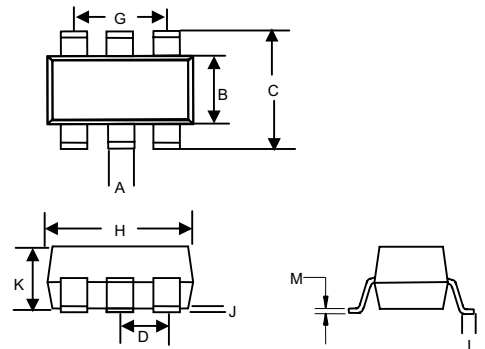
Symbol	Parameter	Value	Unit
<b>N-Channel MOSFET</b>			
V <sub>DS</sub>	Drain-Source Voltage	60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current -Continuous	0.34	A
I <sub>DM</sub>	Drain Current - Pulsed(Note1)	1.36	A
<b>P-Channel MOSFET</b>			
V <sub>DS</sub>	Drain-Source Voltage	-50	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current -Continuous	-0.18	A
I <sub>DM</sub>	Drain Current – Pulsed (Note1)	-0.7	A
<b>Power Dissipation, Temperature and Thermal Resistance</b>			
P <sub>D</sub>	Power Dissipation	0.15	W
R <sub>θJA</sub>	Thermal Resistance from Junction to Ambient (Note2)	833	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C
T <sub>L</sub>	Lead Temperature	260	°C

### Equivalent circuit

Marking :75



### SOT-363



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.006	.014	0.15	0.35	
B	.045	.053	1.15	1.35	
C	.085	.096	2.15	2.45	
D	.026		0.65Nominal		
G	.047	.055	1.20	1.40	
H	.071	.087	1.80	2.20	
J	---	.004	---	0.10	
K	.031	.043	0.80	1.10	
L	.010	.018	0.26	0.46	
M	.003	.006	0.08	0.15	

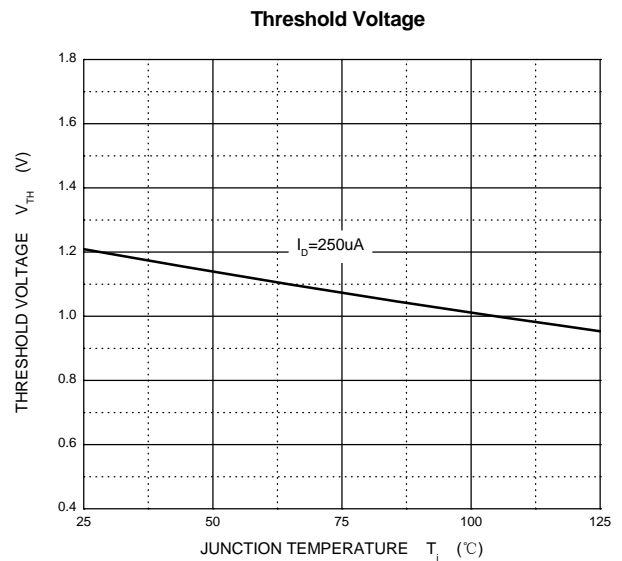
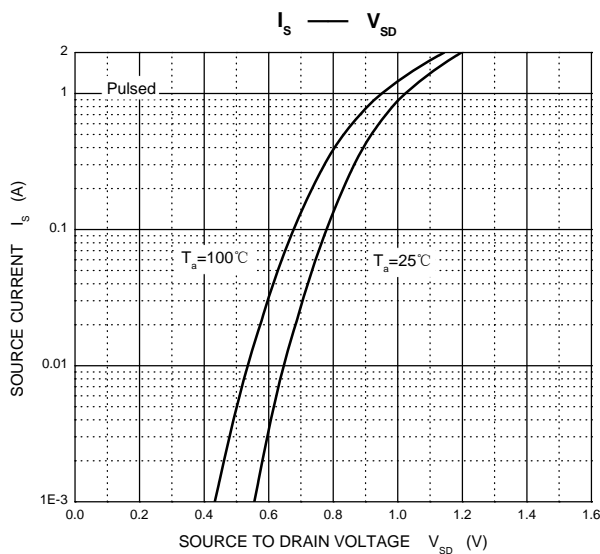
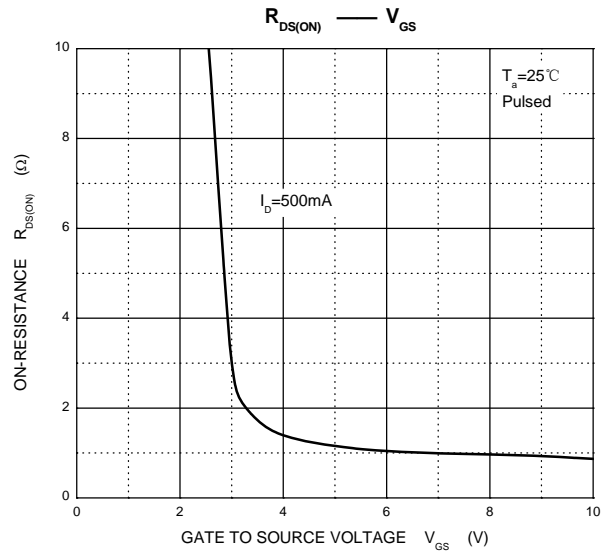
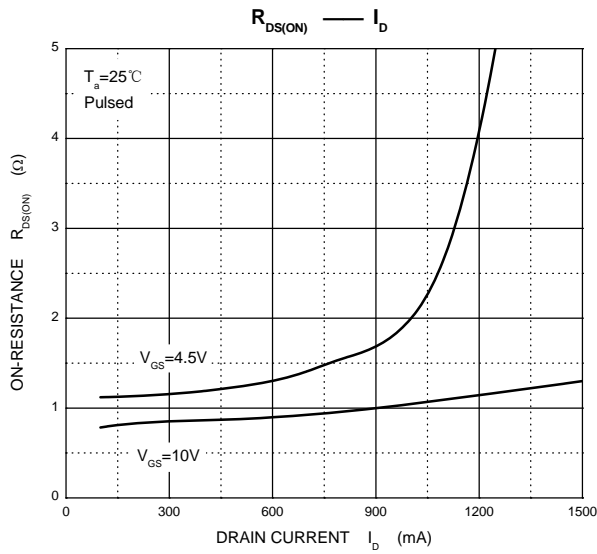
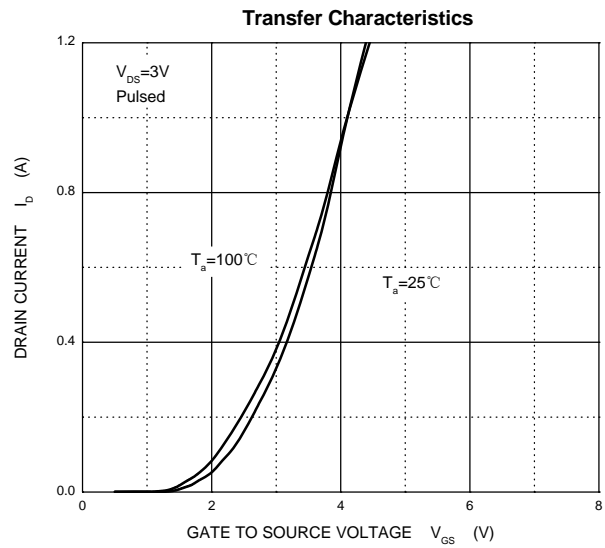
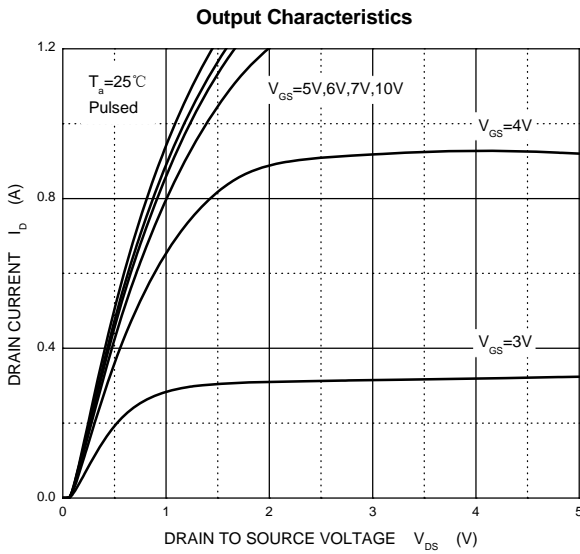
**Electrical characteristics (T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>N- Channel MOSFET</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±10	μA
		V <sub>GS</sub> =±10V, V <sub>DS</sub> = 0V			±200	nA
		V <sub>GS</sub> =±5V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage (note 3)	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =1mA	1	1.3	2.5	V
Drain-source on-resistance (note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.2A		1.1	5.3	Ω
		V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A		0.9	5	Ω
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =0.3A, V <sub>GS</sub> = 0V			1.5	v
<b>DYNAMIC PARAMETERS (note 4)</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f =1MHz			40	pF
Output Capacitance	C <sub>oss</sub>				30	pF
Reverse Transfer Capacitance	C <sub>rss</sub>				10	pF
<b>SWITCHING PARAMETERS (note 4)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V,			10	ns
Turn-off delay time	t <sub>d(off)</sub>	R <sub>L</sub> =250Ω, R <sub>GEN</sub> =50Ω,			15	ns
Reverse recovery time	t <sub>rr</sub>	I <sub>S</sub> =300mA;		30		ns
Recovered charge	Q <sub>r</sub>	d <sub>IS</sub> /d <sub>t</sub> =-100A/s; V <sub>GS</sub> =0V; V <sub>R</sub> =25V		30		nC
<b>P- Channel MOSFET</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =-250μA	-50			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =-50V, V <sub>GS</sub> = 0V			-15	μA
		V <sub>DS</sub> =-25V, V <sub>GS</sub> = 0V			-0.1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±10	nA
Gate threshold voltage (note 3)	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.9	-1.62	-2	V
Drain-source on-resistance (note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> =-5V, I <sub>D</sub> =-0.1A		5.5	10	Ω
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-0.1A		4.1	8	Ω
Forward transconductance (note 3)	g <sub>FS</sub>	V <sub>DS</sub> =-25V, I <sub>D</sub> =-0.1A	0.05			S
<b>DYNAMIC CHARACTERISTICS (note 4)</b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-5V, V <sub>GS</sub> =0V, f =1MHz		30		pF
Output capacitance	C <sub>oss</sub>			10		pF
Reverse transfer capacitance	C <sub>rss</sub>			5		pF
<b>SWITCHING CHARACTERISTICS (note 4)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, R <sub>L</sub> =50Ω, I <sub>D</sub> =-2.5A		2.5		ns
Turn-on rise time	t <sub>r</sub>			1		ns
Turn-off delay time	t <sub>d(off)</sub>			16		ns
Turn-off fall time	t <sub>f</sub>			8		ns
<b>SOURCE-DRAIN DIODE CHARACTERISTICS(note 4)</b>						
Continuous Current	I <sub>S</sub>	I <sub>S</sub> =-0.13A, V <sub>GS</sub> = 0V			-0.18	A
Pulsed Current	I <sub>SM</sub>				-0.7	A
Diode forward voltage (note 3)	V <sub>DS</sub>				-2.2	v

- Note:**
- Surface mounted on FR-4 board using minimum pad size, 1oz copper
  - Repetitive Rating: Pulse width limited by maximum junction temperature.
  - Pulse test: pulse width ≤ 300μ s, duty cycle ≤ 2%
  - These parameters have no way to verify.

# Typical Characteristics

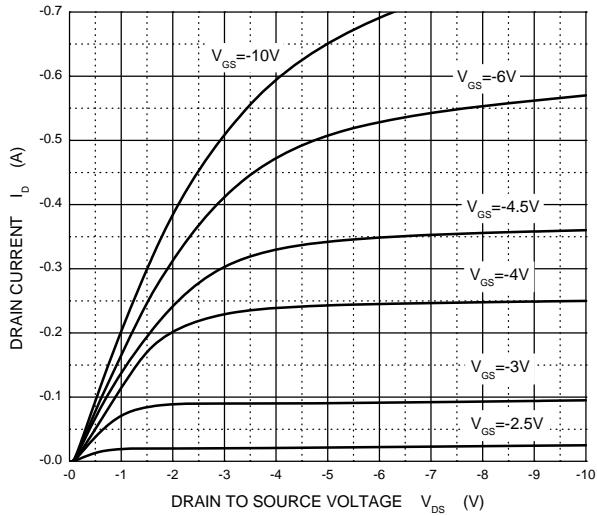
N-Channel MOS



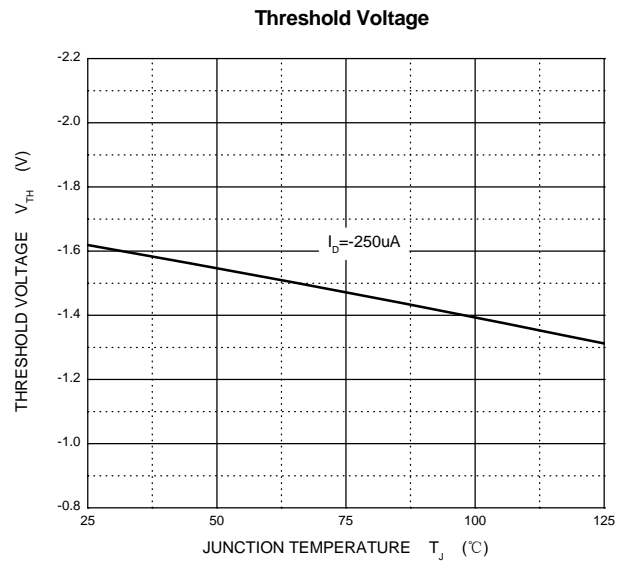
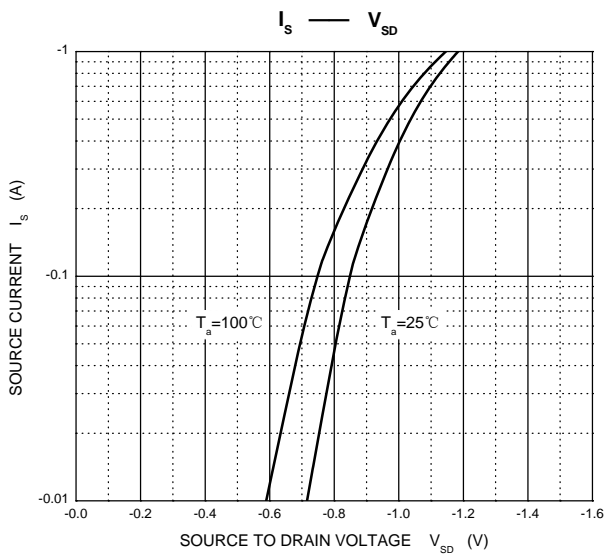
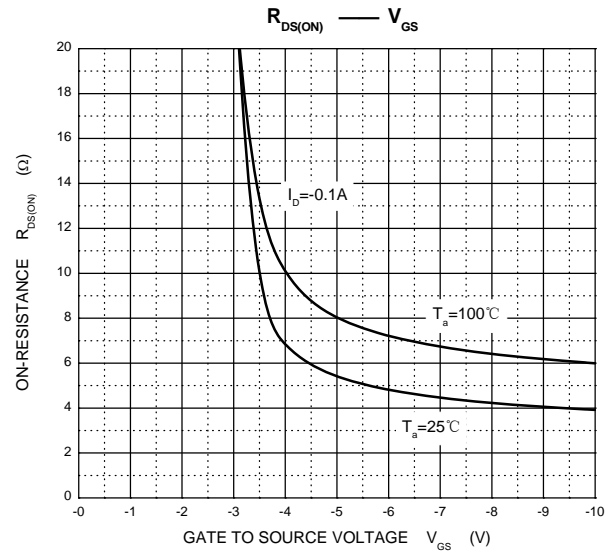
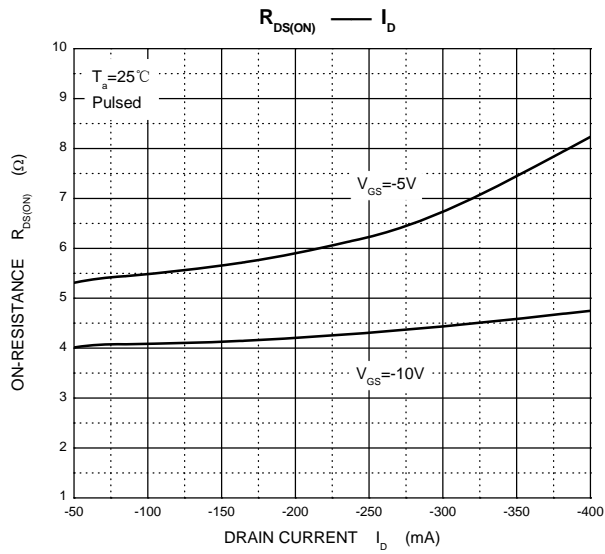
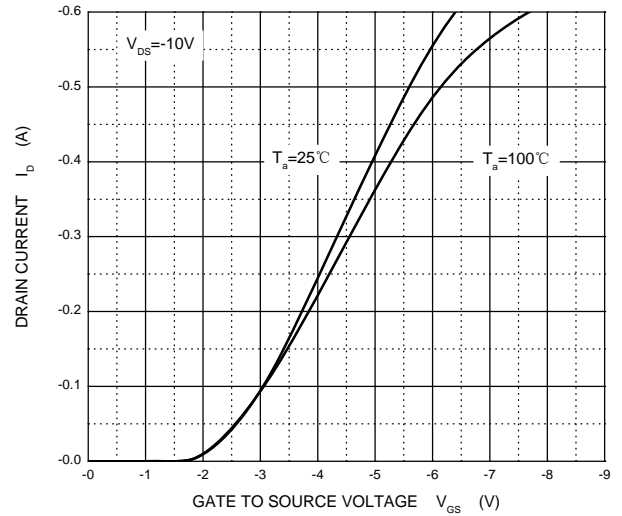
## Typical Characteristics

P-Channel MOS

**Output Characteristics**



**Transfer Characteristics**





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### Ordering Information :

Device	Packing
Part Number-TP	Tape&Reel; 3Kpcs/Reel

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